TOSHIBA Field-Effect Transistor Silicon N-Channel MOS Type

SSM3K38MFV

- High-Speed Switching Applications
- Analog Switch Applications
- 1.2V drive

• Low ON-resistance : R_{on} = 20 Ω (max) (@V_{GS} = 1.2 V)

: $R_{On} = 8 \Omega \text{ (max) } (@V_{GS} = 1.5 \text{ V})$: $R_{On} = 4 \Omega \text{ (max) } (@V_{GS} = 2.5 \text{ V})$: $R_{On} = 3 \Omega \text{ (max) } (@V_{GS} = 4.0 \text{ V})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit		
Drain-source voltage	V _{DSS}	20	V		
Gate-source voltage		V_{GSS}	±10	V	
Drain current	DC	ΙD	180	mA	
	Pulse	I_{DP}	360	IIIA	
Drain power dissipation		P _D (Note 1)	150	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature		T _{stg}	−55 ~ 150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling

 $\label{lem:precautions} Precautions"/\text{`Derating Concept and Methods''}) \ and \ individual \ reliability \ data \ (i.e. \ reliability \ test \ report \ and \ estimated \ failure \ rate, \ etc).$

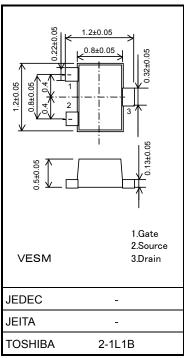
Note 1: Mounted on an FR4 board (25.4 mm \times 25.4 mm \times 1.6 t,Cu Pad:0.585mm²)

Electrical Characteristics (Ta = 25°C)

Charac	cteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage curre	ent	I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$		_	_	±1	μΑ
Drain-source brea	kdown voltage	V (BR) DSS	$I_D = 0.1 \text{ mA}, V_{GS} = 0 \text{ V}$		20	_	_	V
Drain cutoff curren	t	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$		_	_	1	μΑ
Gate threshold vol	tage	V_{th}	$V_{DS}=3\;V,\;I_D=1\;mA$		0.4	_	1.0	V
Forward transfer a	dmittance	Y _{fs}	$V_{DS}=3\ V,\ I_D=50\ mA$	(Note2)	115	_	_	mS
Drain-source ON-resistance		RDS (ON)	$I_D = 50$ mA, $V_{GS} = 4$ V	(Note2)	_	1.5	3	Ω
			$I_D = 50 \text{ mA}, V_{GS} = 2.5 \text{ V}$	(Note2)	_	2	4	
			$I_D = 5 \text{ mA}, V_{GS} = 1.5 \text{ V}$	(Note2)	_	3	8	
			$I_D = 5$ mA, $V_{GS} = 1.2$ V	(Note2)	_	5	20	
Input capacitance		C _{iss}	V _{DS} = 3 V, V _{GS} = 0 V, f = 1 MHz		_	9.5	_	pF
Reverse transfer capacitance		C _{rss}			_	4.1	_	
Output capacitance	е	Coss]		_	9.5	_	
Switching time	Turn-on time	t _{on}	V _{DD} = 3 V, I _D = 50 mA, V _{GS} = 0 to 2.5 V		_	70	_	ns
	Turn-off time	t _{off}			_	145	_	
Drain-source forward	ard voltage	V _{DSF}	$I_D = -180 \text{ mA}, V_{GS} = 0 \text{ V}$	(Note2)	_	-0.9	-1.2	V

Note 2: Pulse test

Unit: mm

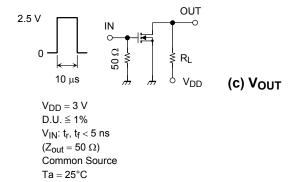


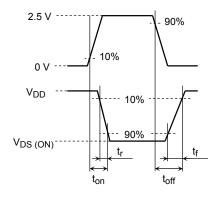
Weight: 1.5 mg (typ.)

Switching Time Test Circuit

(a) Test Circuit

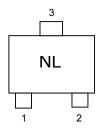


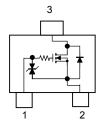




Marking

Equivalent Circuit (top view)





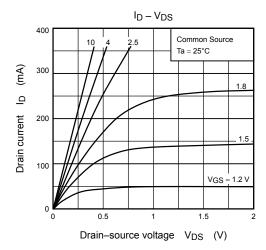
Notice on Usage

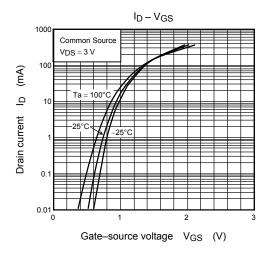
 V_{th} can be expressed as the voltage between gate and source when the low operating current value is I_D = 1 mA for this product. For normal switching operation, $V_{GS (on)}$ requires a higher voltage than V_{th} and $V_{GS (off)}$ requires a lower voltage than V_{th} . (The relationship can be established as follows: $V_{GS (off)} < V_{th} < V_{GS (on)}$.)

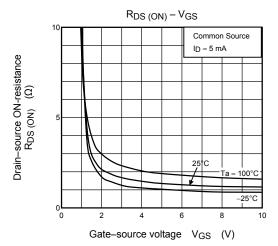
Take this into consideration when using the device.

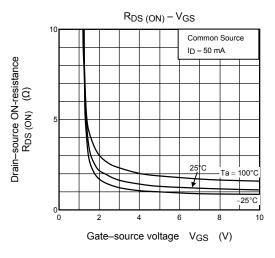
Handling Precaution

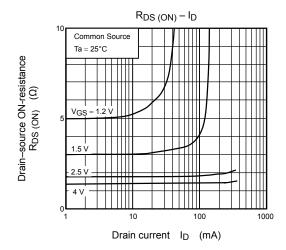
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

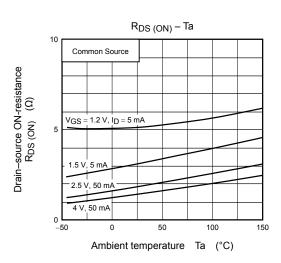




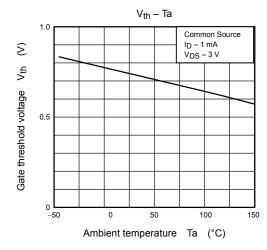


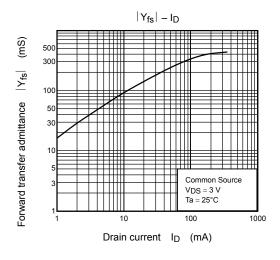


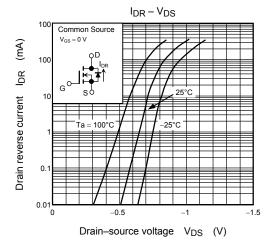


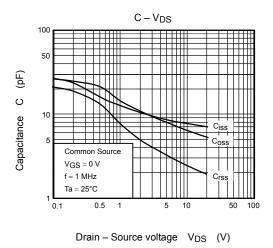


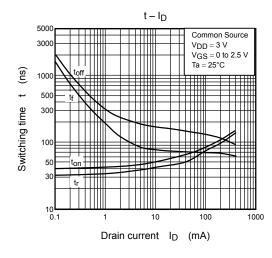
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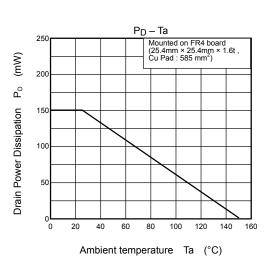












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20070701-EN GENERAL

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